



74LVC373A

OCTAL TRANSPARENT D-TYPE LATCH WITH 3-STATE OUTPUTS

Description

The 74LVC373A provides eight transparent D-type latches. While the latch-enable (LE) input is high, the Q outputs follow the data (D) inputs. When LE is taken low, the Q outputs are latched at the logic levels set up at the D inputs. A buffered output-enable $\overline{(OE)}$ input can be used to place the eight outputs in either a normal logic state (high or low logic levels) or the high-impedance state. In the high-impedance state, the outputs neither load nor drive the bus lines significantly. The high-impedance state and increased drive provide the capability to drive bus lines without interface or pullup components. \overline{OE} does not affect the internal operations of the latches. Old data can be retained or new data can be entered while the outputs are in the high-impedance state.

The device is designed for operation with a power supply range of 1.65V to 3.6V.

The inputs are tolerant to 5.5V allowing this device to be used in a mixed voltage environment. The device is fully specified for partial power down applications using I_{OFF} . The I_{OFF} circuitry disables the output preventing damaging current backflow when the device is powered down.

Features

- Supply Voltage Range from 1.65V to 3.6V
- Sinks or Sources 24mA at V_{CC} = 3V
- CMOS Low Power Consumption
- IOFF Supports Partial Power Down Operation
- Inputs or Outputs Accept Up to 5.5V
- Inputs Can Be Driven by 3.3V or 5V Allowing for Mixed Voltage Applications
- Schmitt Trigger Action at All Inputs
- Typical V_{OLP} (Quiet Output Ground Bounce) Less Than 0.8V with V_{CC} = 3.3V and T_A = +25°C
- Typical V_{OHV} (Quiet Output dynamic VOH) Greater than 2.0V with V_{CC} = 3.3V and T_A = +25°C
- ESD Protection Tested per JESD 22
 - Exceeds 200-V Machine Model (A115)
 - Exceeds 2000-V Human Body Model (A114)
 - Exceeds 1000-V Charged Device Model (C101)
 - Latch-Up Exceeds 250mA per JESD 78, Class II
- All devices are:
 - Totally Lead-Free & Fully RoHS compliant (Notes 1 & 2)
 - Halogen and Antimony Free. "Green" Device (Note 3)

Notes: 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.

- 2. See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen and Antimony free, "Green" and Lead-Free.
- 3. Halogen and Antimony free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.

Pin Assignments



Applications

- General Purpose Logic
- Bus Driving
- Power Down Signal Isolation
- Wide array of products such as:
 - PCs, Notebooks, Netbooks, Ultrabooks
 - Networking Computer Peripherals, Hard Drives, CD/DVD ROM
 - TV, DVD, DVR, Set Top Box



Ordering Information



Part Number	Package	Package	Package	13" Tape	and Reel
Part Number	Code	(Note 4 & 5)	Size	Quantity	Part Number Suffix
74LVC373AT20-13	T20	TSSOP-20	6.4mm X 6.5mm X 1.2mm 0.65 mm lead pitch	2500/Tape & Reel	-13
74LVC373AQ20-13	Q20	V-QFN4525-20	2.5mm X 4.5mm X 0.95mm 0.50 mm lead pitch	2500/Tape & Reel	-13

Notes: 4. Pad layout as shown on Diodes Inc. suggested pad layout document AP02001, which can be found on our website at

http://www.diodes.com/datasheets/ap02001.pdf.

5. V-QFN4525-20 is a JEDEC recognized naming convention that specifies the package thickness category as V and the number 4525 describes the package as 4.5mm X 2.5mm.

Pin Descriptions

Pin Number	Pin Name	Description
1	OE	Output Enable
2	Q1	Latch Output
3	D1	Data Input
4	D2	Data Input
5	Q2	Latch Output
6	Q3	Latch Output
7	D3	Data Input
8	D4	Data Input
9	Q4	Latch Output
10	GND	Ground
11	LE	Latch Enable
12	Q5	Latch Output
13	D5	Data Input
14	D6	Data Input
15	Q6	Latch Output
16	Q7	Latch Output
17	D7	Data Input
18	D8	Data Input
19	Q8	Latch Output
20	Vcc	Supply Voltage

Logic Diagram



Function Table

(Each Latch)							
	INPUTS OUTPUT						
ŌE	LE	D	Q				
L	Н	Н	Н				
L	Н	L	L				
L	L	Х	Q ₀				
Н	Х	Х	Z				



Absolute Maximum Ratings (Notes 6 & 7)

Symbol	Description	Rating	Unit
ESD HBM	Human Body Model ESD Protection	2	kV
ESD CDM	Charged Device Model ESD Protection	1	kV
ESD MM	Machine Model ESD Protection	200	V
Vcc	Supply Voltage Range	-0.5 to +7.0	V
VI	Input Voltage Range	-0.5 to +7.0	V
I _{IK}	Input Clamp Current VI< 0V	-20	mA
I _{OK}	Output Clamp Current V _O < 0V	-50	mA
lo	Continuous Output Current -0.5V < V _O V _{CC} +0.5V	±50	mA
lcc	Continuous Current Through V _{CC}	100	mA
I _{GND}	Continuous Current Through GND	-100	mA
TJ	Operating Junction Temperature	-40 to +150	°C
T _{STG}	Storage Temperature	-65 to +150	°C
P _{TOT}	Total Power Dissipation	500	mW

Notes: 6. Stresses beyond the absolute maximum may result in immediate failure or reduced reliability. These are stress values and device operation should be within recommend values.

7. Forcing the maximum allowed voltage could cause a condition exceeding the maximum current or conversely forcing the maximum current could cause a condition exceeding the maximum voltage. The ratings of both current and voltage must be maintained within the controlled range.

Recommended Operating Conditions (Note 8)

Symbol	Parameter	Conditions	Min	Max	Unit
	Operating	1.65	3.6	V	
V _{CC}	Supply Voltage	Data Retention Only	1.5	—	V
VI	Input Voltage	-	0	5.5	V
Vo	Output Voltage	—	0	V _{CC}	V
		V _{CC} = 1.65V	—	-4	
	Lligh Lovel Output Current	V _{CC} = 2.3V	—	-8	m 4
Іон	High-Level Output Current	V _{CC} = 2.7V	—	-12	mA
		V _{CC} = 3.0V	—	-24	Ī
		V _{CC} = 1.65V	—	4	
		V _{CC} = 2.3V	—	8	
IOL	Low-Level Output Current	V _{CC} = 2.7V	—	12	mA
		V _{CC} = 3.0V	—	24	T
Δt/ΔV	Input Transition Rise or Fall Rate		_	10	ns/V
T _A	Operating Free-Air Temperature		-40	+125	°C

Note: 8. Unused inputs should be held at V_{CC} or ground.



Electrical Characteristics

Symbol	Parameter	Test Conditions	V	T _A = -40°0	C to +85°C	T _A = +85°C	to +125°C	Unit	
Symbol	Parameter	Test Conditions	Vcc	Min	Max	Min	Max	Unit	
			1.65V to 1.95V	V _{CC} X 0.65	—	V _{CC} X 0.65	—		
VIH	High-Level Input Voltage		2.3V to 2.7V	1.7	—	1.7	—	V	
	Voltage		3.0V to 3.6V	2	—	2	—		
			1.65V to 1.95V	—	V _{CC} X 0.35	—	V _{CC} X 0.35		
VIL	Low-Level Input Voltage		2.3V to 2.7V		0.7	—	0.7	V	
	renage		3.0V to 3.6V		0.8	—	0.8		
		I _{OH} = -50µА	1.65V to 3.6V	V _{CC} -0.2	_	V _{CC} -0.3	—		
		I _{OH} = -4mA	1.65V	1.2	—	1.05	—		
Maria	High-Level Output	I _{OH} = -8mA	2.3V	1.7	—	1.65	—		
V _{OH}	Voltage	L = 10mA	2.7V	2.2	—	2.05	—	V	
		I _{OH} = -12mA	3.0V	2.4	—	2.48	_	v	
		I _{OH} = -24mA	3.0V	2.3	—	2.0	_		
		I _{OL} = 100μA	1.65V to 3.6V	—	0.2	—	0.3		
		I _{OL} = 4mA	1.65V	_	0.45	_	0.65		
Vol	Low-Level Output	I _{OL} = 8mA	2.3V	_	0.60	_	0.80	V	
	voltage	I _{OL} = 12mA	2.7V	_	0.40	_	0.60		
		I _{OL} = 24mA	3.0V	_	0.55	_	0.80		
I _{OFF}	Power Down Leakage Current	$V_1 \text{ or } V_0 = 0 \text{ or } 5.5 V$	0V	_	±10	_	20	μA	
lı	Input Current Control Pins	V ₁ = GND or 5.5V	0 to 3.6V	_	±5	—	±20	μA	
I _{OZ}	Z-state Current Including Input Current I/O Pins	$V_1 = GND \text{ or } 5.5V$ $V_0 = 0 \text{ to } 5.5V$	3.6V	_	±5	_	±20	μA	
Icc	Supply Current	$V_{I} = GND \text{ or } V_{CC}, I_{O} = 0$	3.6V		10	—	40	μA	
Δlcc	Additional Supply Current	One input at Vcc-0.6V Io = 0A	2.7V to 3.6V	_	500	_	5000	μA	
Ci	Input Capacitance	$\begin{array}{c c} \hline Control Pins & V_{I} = GND \text{ or} \\ \hline I/O Pins & V_{CC} \end{array}$	0V to 3.6V		ypical ypical	4.0 ty 5.5 ty	•	pF	



Switching Characteristics

Quara had	Demonster	Test		-	T _A = +25°C	;	-40°C to	o +85°C	+85°C to) +125°C	L Incid
Symbol	Parameter	Conditions	V _{cc}	Min	Тур.	Max	Min	Max	Min	Max	Unit
			1.8V ± 0.15V	5.0	2.5		5.0		5.5		
	Pulse Width		2.5V ± 0.3V	4.0	2.0		4.0		4.5		20
tw	LE	Figure 1	2.7V	3.0	1.7		3.0		3.5		ns
			3.3V ± 0.3	3.0	1.5		3.0		3.5		
			1.8V ± 0.15V	4.0	2.0		4.0		4.5		
	Set-up Time D _N to	Eigung (2.5V ± 0.3V	3.0	1.5		3.0		3.5		
t _{su}	LE	Figure 1	2.7V	2.0	1.0		2.0		2.5		ns
			3.3V ± 0.3	2.0	1.0		2.0		2.5		
			1.8V ± 0.15V	3.0	1.5		3.0		3.5		
	Hold Time	Eisen 4	2.5V ± 0.3V	2.0	1.0		2.0		2.5		
t _H	D _N to LE	Figure 1	2.7V	1.5	1.0		1.5		2.0		ns
			3.3V ± 0.3	1.5	1.0		1.5		2.0		
			1.8V ± 0.15V	1	6	12.2	1	12.7	1	16.9	
	Propagation Delay	Eisen 4	2.5V ± 0.3V	1	3.9	7.8	1	8.3	1	8.7	ns
t _{PD}	D_N to Q_N	Figure 1	2.7V	1	4.2	7.8	1	7.3	1	9.5	
			3.3V ± 0.3	1.5	3.8	6.8	1.5	6.3	1.5	8.0	
			1.8V ± 0.15V	1	7	14.8	1	15.3	1	22.5	
	Propagation Delay	Eisen d	2.5V ± 0.3V	1	4.5	10	1	10.5	1	12.4	
t _{PD}	LE to Q _N	Figure 1	2.7V	1	5.4	8.2	1	9.5	1	12.0	ns
			3.3V ± 0.3	1.5	4.4	7.2	1.5	8.5	1.5	11.0	
			1.8V ± 0.15V	1	7.8	16.5	1	17	1	14.2	
	Enable Time	Eisen d	2.5V ± 0.3V	1	4	9	1	9.5	1	8.2	
t _{EN}	\overline{OE} to Q_N	Figure 1	2.7V	1	4.4	8.3	1	8.5	1	10.0	ns
			3.3V ± 0.3	1.7	4.1	7.3	1.7	7.5	1.7	9.0	
			1.8V ± 0.15V	1	7.8	16.5	1	17	1	14.2	
	Disable Time	Eigung (2.5V ± 0.3V	1	4	9	1	9.5	1	8.2	
t _{DIS}	\overline{OE} to Q_N	Figure 1	2.7V	1	4.4	8.3	1	8.5	1	10.0	ns
			3.3V ± 0.3	1.7	4.1	7.3	1.7	7.5	1.7	9.0	
			1.8V ± 0.15V	1	7.8	16.5	1	17	1	14.2	
	Disable Time	Figure 4	2.5V ± 0.3V	1	4	9	1	9.5	1	8.2	
t _{DIS}	\overline{OE} to Q_N	Figure 1	2.7V	1	4.4	8.3	1	8.5	1	10.0	ns
			3.3V ± 0.3V	1.7	4.1	7.3	1.7	7.5	1.7	9.0	
tsk(0)	Output Skew Time		3.3V ± 0.3V		1	1.0				1.5	ns

Operating Characteristics

T _A = +25°C					
Symbol	Parameter	Test Conditions	Vcc	Тур	Unit
	Dower dissinction	F = 10MHz	1.8V ± 0.15V	9.9	
C _{pd}	Power dissipation capacitance per gate	Outputs Enabled	2.5V ± 0.3V	10.2	pF
	capacitance per gate		3.3V ± 0.3V	10.6	

Package Characteristics

U							
Symbol	Parameter	Package	Test Conditions	Min	Тур	Max	Unit
θ _{JA}	Thermal Resistance Junction-to-Ambient	TSSOP-20	(Note 9)	—	74	—	°C/W
θ _{JC}	Thermal Resistance Junction-to-Case	TSSOP-20	(Note 9)	—	15	_	°C/W
θ_{JA}	Thermal Resistance Junction-to-Ambient	V-QFN4525-20	(Note 9)	—	67	—	°C/W
θ_{JC}	Thermal Resistance Junction-to-Case	V-QFN4525-20	(Note 9)	-	20	—	°C/W

Note: 9. Test conditions for TSSOP-20 and V-QFN4525-20: Devices mounted on 4 layer FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout per JESD 51-7.



Parameter Measurement Information



TEST	S1
t _{PLH} /t _{PHL}	Open
t _{PLZ} /t _{PZL}	Vload
t _{PHZ} /t _{PZH}	GND

	In	puts	N.		-	_		
Vcc	VI	t _r /t _f			C∟	R∟	VA	
1.8V±0.15V	V _{cc}	≤2ns	V _{cc} /2	$2 \times V_{CC}$	30pF	1ΚΩ	0.15V	
2.5V±0.2V	V_{CC}	≤2ns	V _{cc} /2	$2 \times V_{CC}$	30pF	500Ω	0.15V	
2.7V	2.7V	≤2.5ns	1.5V	6V	50pF	500Ω	0.3V	
3.3V±0.3V	2.7V	≤2.5ns	1.5V	6V	50pF	500Ω	0.3V	



Voltage Waveform Pulse Duration





A. Includes test lead and test apparatus capacitance. Notes:

- B. All pulses are supplied at pulse repetition rate ≤ 10 MHz.
- C. Inputs are measured separately one transition per measurement.
- D. t_{PLZ} and t_{PHZ} are the same as t_{dis.}
- E. t_{PZL} and t_{PZH} are the same as t_{EN0} F. t_{PLH} and t_{PHL} are the same as $t_{PD.}$

Figure 1 Load Circuit and Voltage Waveforms



Voltage Waveform Enable and Disable Times Low and High Level Enabling



Marking Information

(1) TSSOP20



(2) QFN-20 (V-QFN4525-20)



V-QFN4525-20

74LVC373AQ20



Package Outline Dimensions (All Dimensions in mm)

Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for the latest version.

(1) TSSOP-20



	TSSOP-20								
Dim	Min Max Typ								
Α	-	1.20	-						
A1	0.05	0.15	-						
A2	0.80	1.05	-						
b	0.19	0.30	-						
С	0.09	0.20	-						
D	6.40	6.60	6.50						
E	6.20	6.60	6.40						
E1	4.30	4.50	4.40						
е	0	.65 BSC)						
L	0.45	0.75	0.60						
L1		1.0 REF							
θ1	0°	8°	-						
θ2	10°	14°	12°						
θ3	10°	14°	12°						
All I	Dimensi	ons in r	nm						

(2) QFN-20 (V-QFN4525-20)



V-QFN4525-20				
Dim	Min	Max	Тур	
Α	0.75	0.85	0.80	
A1	0.00	0.05	0.02	
A3	-	-	0.15	
b	0.18	0.30	0.23	
D	4.45	4.55	4.50	
D2	2.85	3.15	3.00	
ш	2.45	2.55	2.50	
E2	0.85	1.15	1.00	
е	0.50BSC			
L	0.30	0.50	0.40	
Z	-	-	0.385	
Z1	-	-	0.885	
All Dimensions in mm				



Suggested Pad Layout

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for the latest version.

(1) TSSOP-20



Dimensions	Value (in mm)	
С	0.650	
Х	0.420	
X1	6.270	
Y	1.789	
Y1	4.160	
Y2	7.720	

(2) QFN-20 (V-QFN4525-20)



Dimensions	Value (in mm)	
С	0.500	
Х	0.330	
X1	0.600	
X2	3.200	
X3	3.830	
X4	4.800	
Y	0.600	
Y1	1.200	
Y2	0.830	
Y3	2.800	



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